# **Small Signal MOSFET**

60 V, 115 mA, N-Channel SOT-23

# **Features**

• Pb-Free Packages are Available

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	Vdc
Drain–Gate Voltage ( $R_{GS} = 1.0 \text{ M}\Omega$ )	$V_{DGR}$	60	Vdc
Drain Current  - Continuous $T_C = 25^{\circ}C$ (Note 1) $T_C = 100^{\circ}C$ (Note 1)  - Pulsed (Note 2)	I <sub>D</sub> I <sub>D</sub>	±115 ±75 ±800	mAdc
Gate-Source Voltage - Continuous - Non-repetitive (t <sub>p</sub> ≤ 50 μs)	V <sub>GS</sub> V <sub>GSM</sub>	±20 ±40	Vdc Vpk

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 3) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate,(Note 4) T <sub>A</sub> = 25°C	P <sub>D</sub>	300	mW mW/°C
Derate above 25°C		2.4	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

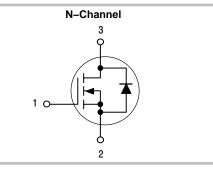
- The Power Dissipation of the package may result in a lower continuous drain current.
- 2. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.
- 3.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 4. Alumina =  $0.4 \times 0.3 \times 0.025$  in 99.5% alumina.



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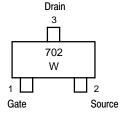
V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> MAX	I <sub>D</sub> MAX
60 V	7.5 Ω @ 10 V, 500 mA	115 mA



# MARKING DIAGRAM & PIN ASSIGNMENT



SOT-23 CASE 318 STYLE 21



702 = Device Code W = Work Week

# ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>	
2N7002LT1	SOT-23	3000 Tape & Reel	
2N7002LT3	001 20	10,000 Tape & Reel	
2N7002LT1G	SOT-23	3000 Tape & Reel	
2N7002LT3G	(Pb-free)	10,000 Tape & Reel	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# 2N7002L

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

С	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						Į.
Drain-Source Breakdown Volt (V <sub>GS</sub> = 0, I <sub>D</sub> = 10 μAdc)	V <sub>(BR)DSS</sub>	60	-	-	Vdc	
Zero Gate Voltage Drain Curre (V <sub>GS</sub> = 0, V <sub>DS</sub> = 60 Vdc)	I <sub>DSS</sub>	- -	- -	1.0 500	μAdc	
Gate-Body Leakage Current, (V <sub>GS</sub> = 20 Vdc)	Forward	I <sub>GSSF</sub>	_	_	100	nAdc
Gate-Body Leakage Current, (V <sub>GS</sub> = -20 Vdc)	Reverse	I <sub>GSSR</sub>	-	-	-100	nAdc
ON CHARACTERISTICS (Not	e 5)					
Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μAdo	)	V <sub>GS(th)</sub>	1.0	_	2.5	Vdc
On–State Drain Current $(V_{DS} \ge 2.0 V_{DS(on)}, V_{GS} = 1.0 V_{DS(on)})$	I <sub>D(on)</sub>	500	-	-	mA	
Static Drain–Source On–State ( $V_{GS} = 10 \text{ Vdc}$ , $I_D = 500 \text{ m}$ . ( $V_{GS} = 5.0 \text{ Vdc}$ , $I_D = 50 \text{ mA}$	V <sub>DS(on)</sub>	- -	- -	3.75 0.375	Vdc	
Static Drain–Source On–State ( $V_{GS} = 10 \text{ V}, I_D = 500 \text{ mAd}$ ( $V_{GS} = 5.0 \text{ Vdc}, I_D = 50 \text{ mAd}$	r <sub>DS(on)</sub>	- - -	- - -	7.5 13.5 7.5	Ohms	
Forward Transconductance $(V_{DS} \ge 2.0 \ V_{DS(on)}, \ I_D = 200 \ m$	9FS	80	_	13.5	mmhos	
DYNAMIC CHARACTERISTIC	cs					
Input Capacitance (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f =	= 1.0 MHz)	C <sub>iss</sub>	-	_	50	pF
Output Capacitance (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f =	C <sub>oss</sub>	-	-	25	pF	
Reverse Transfer Capacitance (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f =	C <sub>rss</sub>	-	-	5.0	pF	
SWITCHING CHARACTERIS	TICS (Note 5)					
Turn-On Delay Time	$(V_{DD} = 25 \text{ Vdc}, I_D \cong 500 \text{ mAdc},$	t <sub>d(on)</sub>	_	_	20	ns
Turn-Off Delay Time	$R_G = 25 \Omega$ , $R_L = 50 \Omega$ , $V_{gen} = 10 V$ )	t <sub>d(off)</sub>	-	_	40	ns
BODY-DRAIN DIODE RATING	GS					
Diode Forward On–Voltage (I <sub>S</sub> = 11.5 mAdc, V <sub>GS</sub> = 0 V	V <sub>SD</sub>	-	_	-1.5	Vdc	
Source Current Continuous (Body Diode)	Is	-	-	-115	mAdc	
Source Current Pulsed		I <sub>SM</sub>	_	_	-800	mAdc

<sup>5.</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

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# TYPICAL ELECTRICAL CHARACTERISTICS

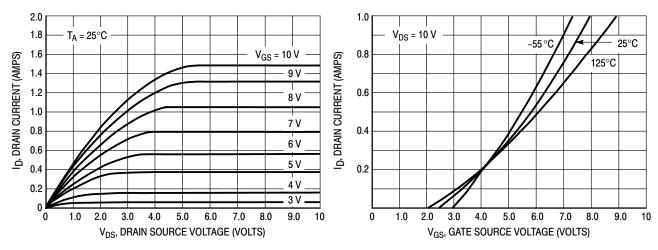


Figure 1. Ohmic Region

Figure 2. Transfer Characteristics

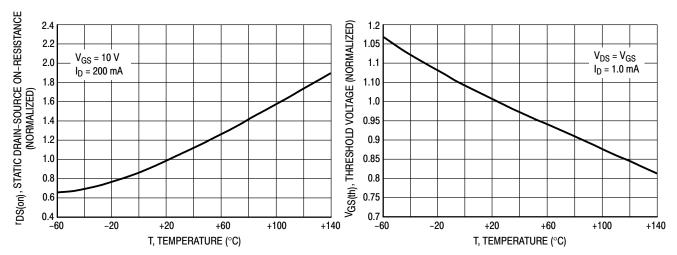


Figure 3. Temperature versus Static Drain–Source On–Resistance

Figure 4. Temperature versus Gate Threshold Voltage

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### PACKAGE DIMENSIONS

# SOT-23 (TO-236) CASE 318-08 **ISSUE AH**

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#### NOTES:

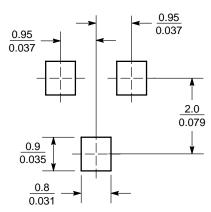
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS
  IS THE MINIMUM THICKNESS OF BASE MATERIAL
- 4. 318-03 AND -07 OBSOLETE, NEW STANDARD

	INC	HES	MILLIN	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX		
Α	0.1102	0.1197	2.80	3.04		
В	0.0472	0.0551	1.20	1.40		
C	0.0350	0.0440	0.89	1.11		
D	0.0150	0.0200	0.37	0.50		
G	0.0701	0.0807	1.78	2.04		
Н	0.0005	0.0040	0.013	0.100		
J	0.0034	0.0070	0.085	0.177		
K	0.0140	0.0285	0.35	0.69		
L	0.0350	0.0401	0.89	1.02		
S	0.0830	0.1039	2.10	2.64		
V	0.0177	0.0236	0.45	0.60		

STYLE 21:

- PIN 1. GATE 2. SOUR
  - SOURCE DRAIN

## **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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